

# BLF6G38-25; BLF6G38S-25

WiMAX power LDMOS transistor

Rev. 02 — 23 December 2008

Product data sheet

## 1. Product profile

### 1.1 General description

25 W LDMOS power transistor for base station applications at frequencies from 3400 MHz to 3800 MHz.

**Table 1. Typical performance**

Typical RF performance at  $T_{case} = 25\text{ }^{\circ}\text{C}$  in a class-AB production test circuit.

Mode of operation	f (MHz)	V <sub>DS</sub> (V)	P <sub>L(AV)</sub> (W)	G <sub>p</sub> (dB)	η <sub>D</sub> (%)	ACPR <sub>885k</sub> (dBc)	ACPR <sub>1980k</sub> (dBc)
1-carrier N-CDMA <sup>[1]</sup>	3400 to 3600	28	4.5	15	24	-45 <sup>[2]</sup>	-61 <sup>[2]</sup>

[1] Single carrier IS-95 with pilot, paging, sync and 6 traffic channels (Walsh codes 8 - 13). PAR = 9.7 dB at 0.01 % probability on the CCDF. Channel bandwidth is 1.2288 MHz.

[2] Measured within 30 kHz bandwidth.

### 1.2 Features

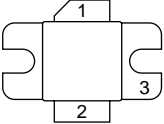
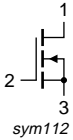
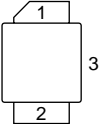
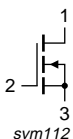
- Typical 1-carrier N-CDMA performance (single carrier IS-95 with pilot, paging, sync and 6 traffic channels [Walsh codes 8 - 13]. PAR = 9.7 dB at 0.01 % probability on the CCDF. Channel bandwidth is 1.2288 MHz) at a frequency of 3400 MHz, 3500 MHz and 3600 MHz, a supply voltage of 28 V and an I<sub>Dq</sub> of 225 mA:
  - ◆ Average output power = 4.5 W
  - ◆ Power gain = 15 dB
  - ◆ Drain efficiency = 24 %
  - ◆ ACPR<sub>885k</sub> = -45 dBc in 30 kHz bandwidth
- Easy power control
- Integrated ESD protection
- Excellent ruggedness
- High efficiency
- Excellent thermal stability
- Designed for broadband operation (3400 MHz to 3800 MHz)
- Internally matched for ease of use
- Compliant to Directive 2002/95/EC, regarding Restriction of Hazardous Substances (RoHS)

### 1.3 Applications

- RF power amplifiers for base stations and multicarrier applications in the 3400 MHz to 3800 MHz frequency range

## 2. Pinning information

**Table 2. Pinning**

Pin	Description	Simplified outline	Graphic symbol
<b>BLF6G38-25 (SOT608A)</b>			
1	drain		 sym112
2	gate		
3	source		
<b>BLF6G38S-25 (SOT608B)</b>			
1	drain		 sym112
2	gate		
3	source		

[1] Connected to flange.

## 3. Ordering information

**Table 3. Ordering information**

Type number	Package		
	Name	Description	Version
BLF6G38-25	-	flanged ceramic package; 2 mounting holes; 2 leads	SOT608A
BLF6G38S-25	-	ceramic earless flanged package; 2 leads	SOT608B

## 4. Limiting values

**Table 4. Limiting values**

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
$V_{DS}$	drain-source voltage		-	65	V
$V_{GS}$	gate-source voltage		-0.5	+13	V
$I_D$	drain current		-	8.2	A
$T_{stg}$	storage temperature		-65	+150	°C
$T_j$	junction temperature		-	200	°C

## 5. Thermal characteristics

**Table 5. Thermal characteristics**

Symbol	Parameter	Conditions	Type	Typ	Max	Unit
$R_{th(j-case)}$	thermal resistance from junction to case	$T_{case} = 80\text{ °C};$ $P_L = 25\text{ W}$	BLF6G38-25	1.8	-	K/W
			BLF6G38S-25	1.8	-	K/W

## 6. Characteristics

**Table 6. Characteristics**  
*T<sub>j</sub> = 25 °C unless otherwise specified.*

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V <sub>(BR)DSS</sub>	drain-source breakdown voltage	V <sub>GS</sub> = 0 V; I <sub>D</sub> = 0.4 mA	65	-	-	V
V <sub>GS(th)</sub>	gate-source threshold voltage	V <sub>DS</sub> = 10 V; I <sub>D</sub> = 40 mA	1.4	2	2.4	V
I <sub>DSS</sub>	drain leakage current	V <sub>GS</sub> = 0 V; V <sub>DS</sub> = 28 V	-	-	1.5	μA
I <sub>DSX</sub>	drain cut-off current	V <sub>GS</sub> = V <sub>GS(th)</sub> + 3.75 V; V <sub>DS</sub> = 10 V	6	8.2	-	A
I <sub>GSS</sub>	gate leakage current	V <sub>GS</sub> = +11 V; V <sub>DS</sub> = 0 V	-	-	150	nA
g <sub>fs</sub>	forward transconductance	V <sub>DS</sub> = 10 V; I <sub>D</sub> = 1.4 A	-	2.8	-	S
R <sub>DS(on)</sub>	drain-source on-state resistance	V <sub>GS</sub> = V <sub>GS(th)</sub> + 3.75 V; I <sub>D</sub> = 1.4 A	-	0.37	0.58	Ω
C <sub>rs</sub>	feedback capacitance	V <sub>GS</sub> = 0 V; V <sub>DS</sub> = 28 V; f = 1 MHz	-	0.59	-	pF

## 7. Application information

**Table 7. Application information**

*Mode of operation: 1-carrier N-CDMA; single carrier IS-95 with pilot, paging, sync and 6 traffic channels (Walsh codes 8 - 13); PAR = 9.7 dB at 0.01 % probability on the CCDF; channel bandwidth is 1.2288 MHz; f<sub>1</sub> = 3400 MHz; f<sub>2</sub> = 3500 MHz; f<sub>3</sub> = 3600 MHz; RF performance at V<sub>DS</sub> = 28 V; I<sub>Dq</sub> = 225 mA; T<sub>case</sub> = 25 °C; unless otherwise specified, in a class-AB production circuit.*

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
G <sub>p</sub>	power gain	P <sub>L(AV)</sub> = 4.5 W	12.5	15	-	dB
RL <sub>in</sub>	input return loss	P <sub>L(AV)</sub> = 4.5 W	-	-10	-	dB
η <sub>D</sub>	drain efficiency	P <sub>L(AV)</sub> = 4.5 W	22	24	-	%
ACPR <sub>885k</sub>	adjacent channel power ratio (885 kHz)	P <sub>L(AV)</sub> = 4.5 W <a href="#">[1]</a>	-	-45	-40	dBc
ACPR <sub>1980k</sub>	adjacent channel power ratio (1980 kHz)	P <sub>L(AV)</sub> = 4.5 W <a href="#">[1]</a>	-	-61	-56	dBc

[1] Measured within 30 kHz bandwidth.

### 7.1 Ruggedness in class-AB operation

The BLF6G38-25 and BLF6G38S-25 are capable of withstanding a load mismatch corresponding to VSWR = 10 : 1 through all phases under the following conditions: V<sub>DS</sub> = 28 V; I<sub>Dq</sub> = 225 mA; P<sub>L</sub> = P<sub>L(1dB)</sub>; f = 3600 MHz.

7.2 NXP WiMAX signal

7.2.1 WiMAX signal description

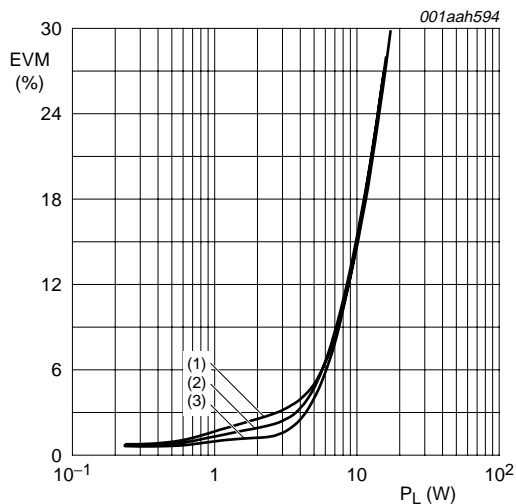
frame duration = 5 ms; bandwidth = 10 MHz; sequency = 1 frame;  
 frequency band = WCS; sampling rate = 11.2 MHz;  $n = 8 / 7$ ;  $G = T_g / T_b = 1 / 8$ ;  
 FFT = 1024; zone type = PUSC;  $\delta = 97.7 \%$ ; number of symbols = 46;  
 number of subchannels = 30; PAR = 9.5 dB.

Preamble: 1 symbol  $\times$  30 subchannels;  $P_L = P_{L(nom)} + 3.86 \text{ dB}$

Table 8. Frame structure

Frame contents	Modulation technique	Data length
Zone 0 FCH 2 symbols $\times$ 4 subchannels	QPSK1/2	3
Zone 0 data 2 symbols $\times$ 26 subchannels	64QAM3/4	692
Zone 0 data 44 symbols $\times$ 30 subchannels	64QAM3/4	10000

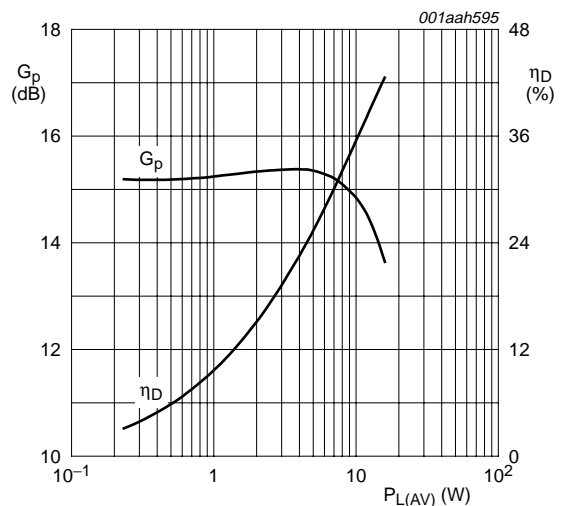
7.2.2 Graphs



$V_{DS} = 28 \text{ V}$ ;  $I_{Dq} = 225 \text{ mA}$ ; OFDMA signal;  
 frame duration = 5 ms; bandwidth = 10 MHz;  
 frequency band = WCS;  $n = 28 / 25$ ;  $G = 1 / 8$ ;  
 FFT = 1024; zone type = PUSC;  
 number of symbols = 46; number of subchannels = 30.

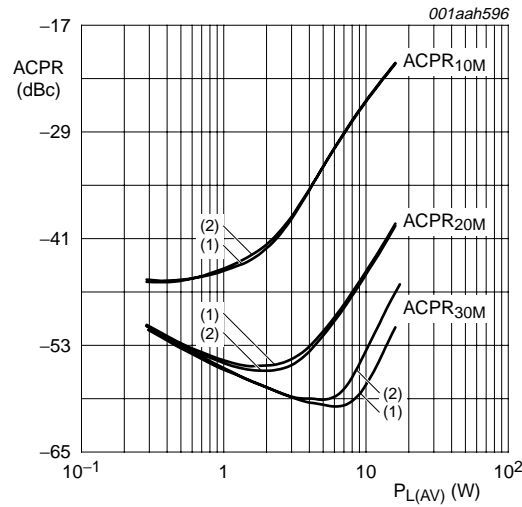
(1)  $f = 3400 \text{ MHz}$   
 (2)  $f = 3500 \text{ MHz}$   
 (3)  $f = 3600 \text{ MHz}$

Fig 1. EVM as function of load power; typical values



$V_{DS} = 28 \text{ V}$ ;  $I_{Dq} = 225 \text{ mA}$ ;  $f = 3500 \text{ MHz}$ ;  
 OFDMA signal; frame duration = 5 ms;  
 bandwidth = 10 MHz; frequency band = WCS;  
 $n = 28 / 25$ ;  $G = 1 / 8$ ; FFT = 1024; zone type = PUSC;  
 number of symbols = 46; number of subchannels = 30.

Fig 2. Power gain and drain efficiency as functions of average load power; typical values



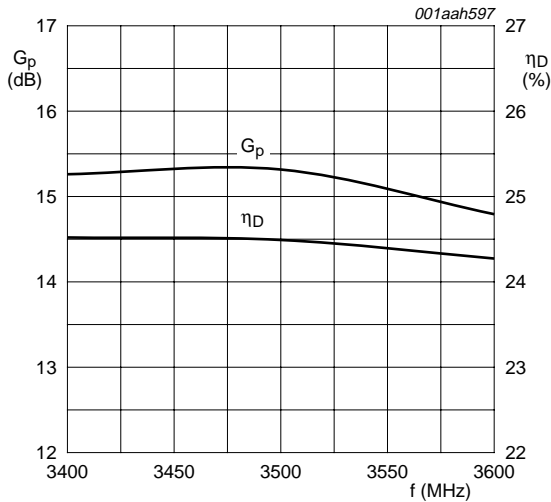
$V_{DS} = 28\text{ V}$ ;  $I_{Dq} = 225\text{ mA}$ ;  $f = 3500\text{ MHz}$ ; OFDMA signal; frame duration = 5 ms; bandwidth = 10 MHz; frequency band = WCS;  $n = 28 / 25$ ;  $G = 1 / 8$ ; FFT = 1024; zone type = PUSC; number of symbols = 46; number of subchannels = 30.

- (1) Low frequency component
- (2) High frequency component

Fig 3. Adjacent channel power ratio as function of average load power; typical values

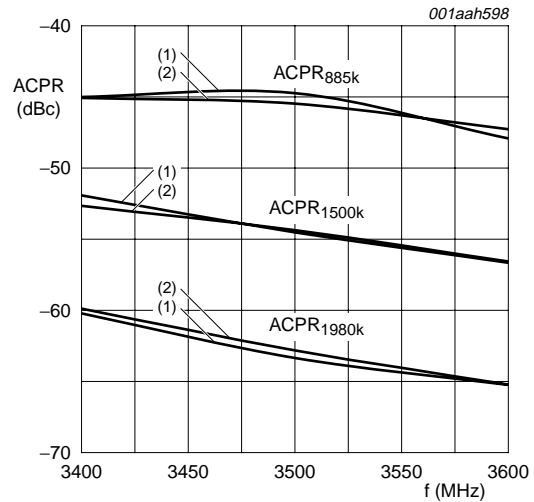
### 7.3 Single carrier N-CDMA broadband performance at 9 W average

#### 7.3.1 Graphs



$P_{L(AV)} = 4.5\text{ W}$ .

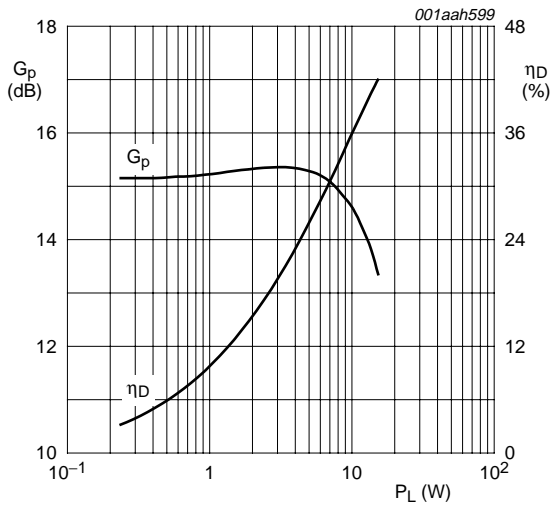
Fig 4. Power gain and drain efficiency as functions of frequency; typical values



$V_{DS} = 28\text{ V}$ ;  $I_{Dq} = 350\text{ mA}$ ;  $P_{L(AV)} = 4.5\text{ W}$ ; single carrier N-CDMA; PAR = 9.7 dB at 0.01 % probability; IBW = 30 kHz.

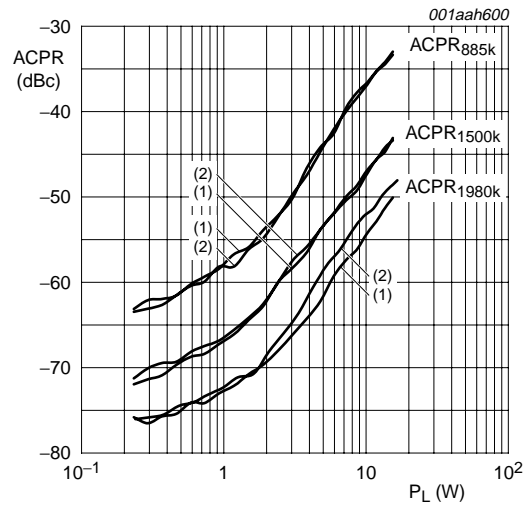
- (1) Low frequency component
- (2) High frequency component

Fig 5. Adjacent channel power ratio as function of frequency; typical values



$V_{DS} = 28\text{ V}$ ;  $I_{DQ} = 225\text{ mA}$ ;  $f = 3500\text{ MHz}$ ; single carrier N-CDMA; PAR = 9.7 dB at 0.01 % probability; channel bandwidth = 1.23 MHz; IBW = 30 kHz.

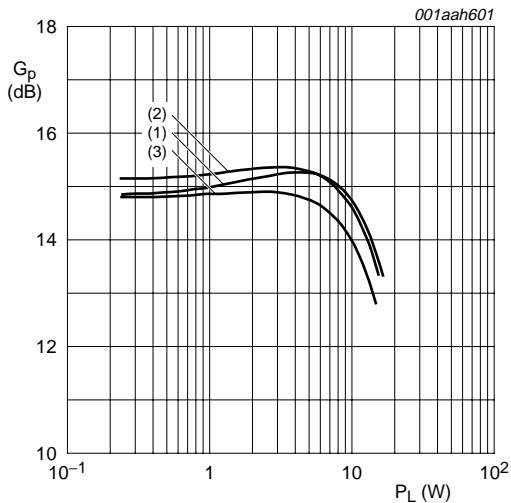
Fig 6. Power gain and drain efficiency as functions of load power; typical values



$V_{DS} = 28\text{ V}$ ;  $I_{DQ} = 225\text{ mA}$ ;  $f = 3500\text{ MHz}$ ; single carrier N-CDMA; PAR = 9.7 dB at 0.01 % probability; channel bandwidth = 1.23 MHz; IBW = 30 kHz.

- (1) Low frequency component
- (2) High frequency component

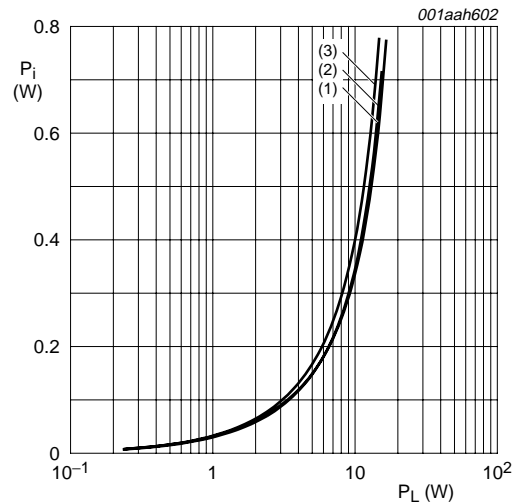
Fig 7. Adjacent channel power ratio as function of average load power; typical values



$V_{DS} = 28\text{ V}$ ;  $I_{DQ} = 225\text{ mA}$ ; single carrier N-CDMA; PAR = 9.7 dB at 0.01 % probability; channel bandwidth = 1.23 MHz; IBW = 30 kHz.

- (1)  $f = 3400\text{ MHz}$
- (2)  $f = 3500\text{ MHz}$
- (3)  $f = 3600\text{ MHz}$

Fig 8. Power gain as function of load power; typical values

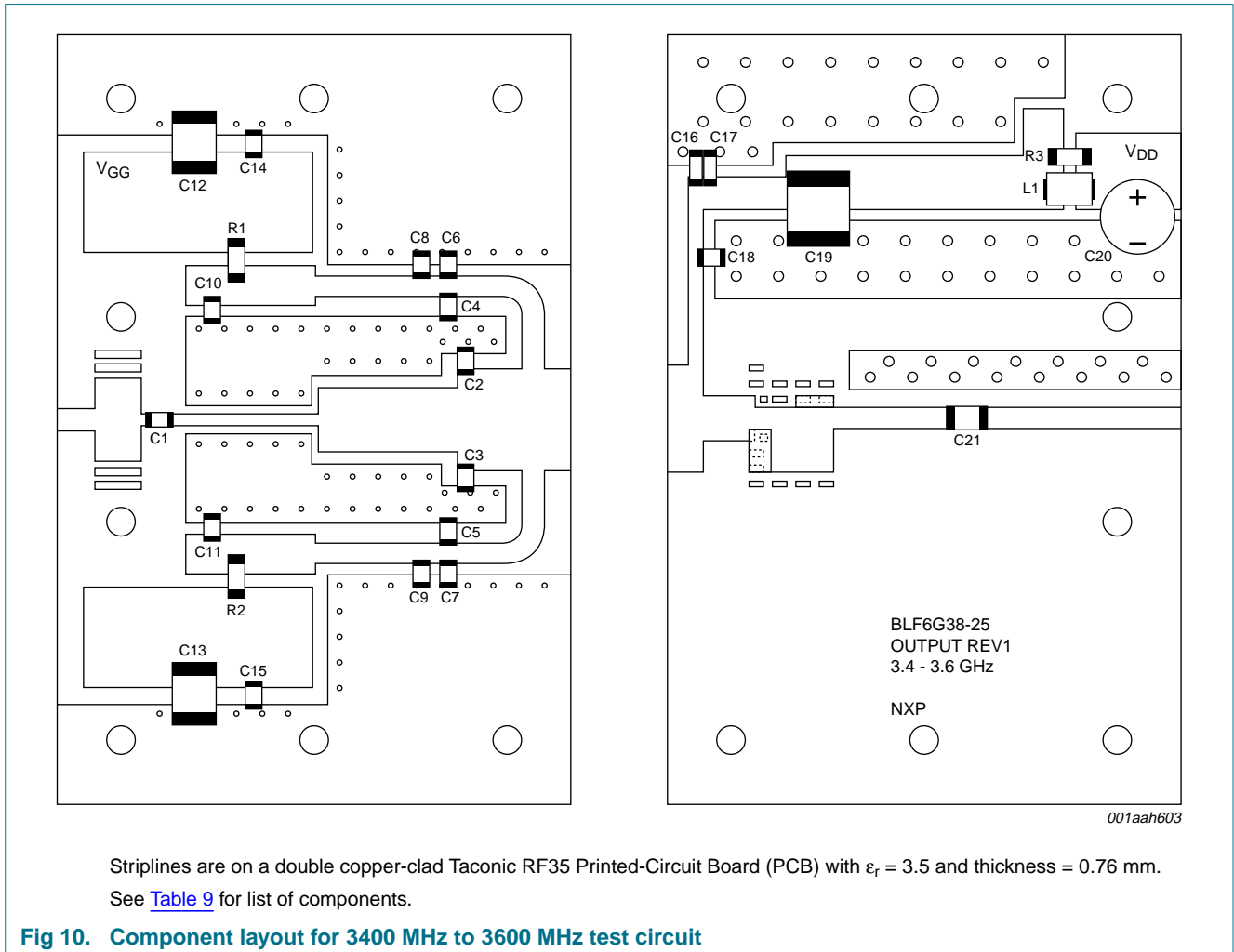


$V_{DS} = 28\text{ V}$ ;  $I_{DQ} = 225\text{ mA}$ ; single carrier N-CDMA; PAR = 9.7 dB at 0.01 % probability; channel bandwidth = 1.23 MHz; IBW = 30 kHz.

- (1)  $f = 3400\text{ MHz}$
- (2)  $f = 3500\text{ MHz}$
- (3)  $f = 3600\text{ MHz}$

Fig 9. Input power as function of load power; typical values

**8. Test information**



**Table 9. List of components (see [Figure 10](#))**

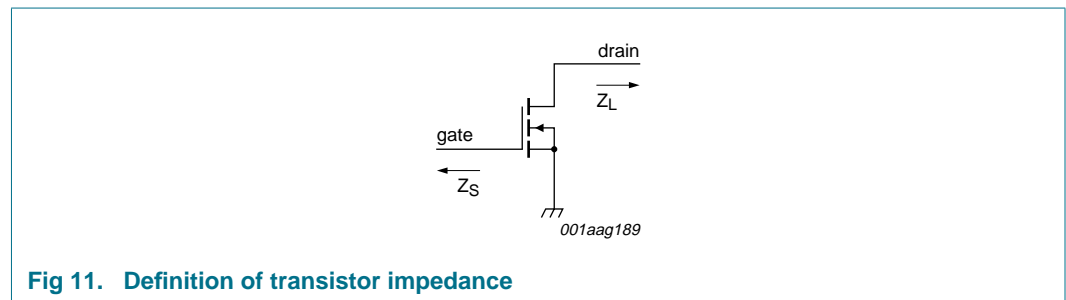
Component	Description	Value	Remarks
C1	multilayer ceramic chip capacitor	22 pF	ATC 100A or equivalent
C2, C3	multilayer ceramic chip capacitor	3 pF	ATC 100A or equivalent
C4, C5, C6, C7, C8, C9, C18	multilayer ceramic chip capacitor	10 pF	ATC 100A or equivalent
C10, C11	multilayer ceramic chip capacitor	24 pF	ATC 100A or equivalent
C12, C13	multilayer ceramic chip capacitor	4.7 $\mu$ F; 50 V	TDK C4532X7R1H475M or equivalent
C14, C15	multilayer ceramic chip capacitor	1 nF	ATC 700A or equivalent
C16, C17	multilayer ceramic chip capacitor	100 nF	Vishay VJ1206Y104KXB or equivalent
C19	multilayer ceramic chip capacitor	10 $\mu$ F; 50 V	TDK C5750X7R1H106M or equivalent
C20	electrolytic capacitor	470 $\mu$ F; 63 V	
C21	multilayer ceramic chip capacitor	10 pF	ATC 100B or equivalent

**Table 9.** List of components (see [Figure 10](#)) ...continued

Component	Description	Value	Remarks
L1	ferrite SMD bead	-	Ferroxcube BDS3/3/4.6-4S2 or equivalent
R1, R2	SMD resistor	20 Ω	SMD 1206
R3	SMD resistor	9.1 Ω	SMD 1206

**Table 10.** Measured test circuit impedances

f MHz	Z <sub>S</sub> Ω	Z <sub>L</sub> Ω
3400	14.65 + j29.87	13.46 + j3.58
3450	14.16 + j28.69	13.56 + j4.12
3500	14.56 + j30.52	13.76 + j4.74
3550	17.49 + j30.11	13.97 + j5.41
3600	15.50 + j29.36	14.16 + j5.95



**Fig 11.** Definition of transistor impedance



**9. Package outline**

Flanged ceramic package; 2 mounting holes; 2 leads

SOT608A

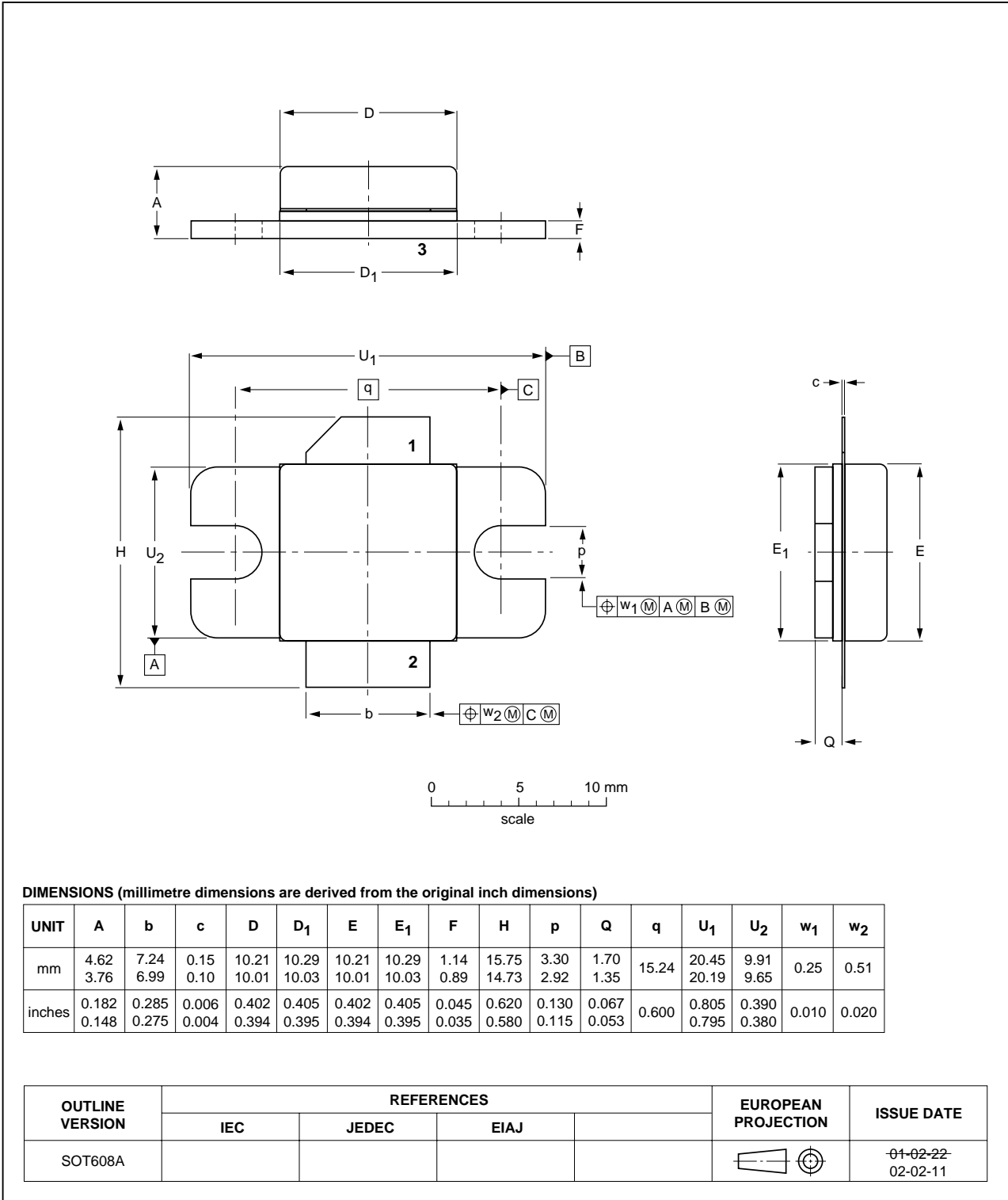


Fig 12. Package outline SOT608A

Ceramic earless flanged package; 2 leads

SOT608B

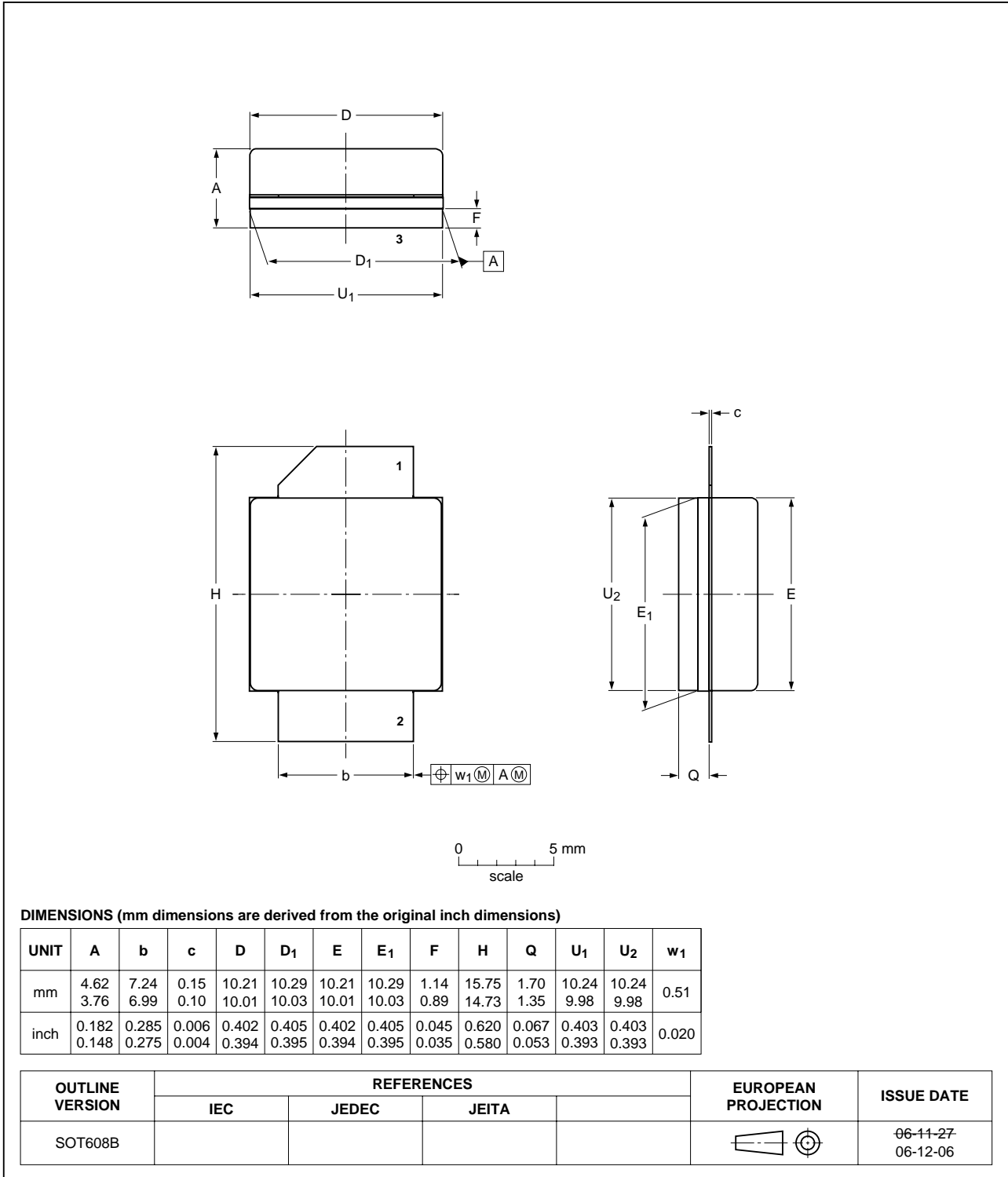


Fig 13. Package outline SOT608B

## 10. Abbreviations

**Table 11. Abbreviations**

Acronym	Description
CCDF	Complementary Cumulative Distribution Function
CW	Continuous Wave
ESD	ElectroStatic Discharge
EVM	Error Vector Magnitude
FCH	Frame Control Header
FFT	Fast Fourier Transform
IBW	Instantaneous BandWidth
IS-95	Interim Standard 95
LDMOS	Laterally Diffused Metal-Oxide Semiconductor
N-CDMA	Narrowband Code Division Multiple Access
OFDMA	Orthogonal Frequency Division Multiple Access
PAR	Peak-to-Average power Ratio
PUSC	Partial Usage of SubChannels
RF	Radio Frequency
QAM	Quadrature Amplitude Modulation
QPSK	Quadrature Phase Shift Keying
SMD	Surface Mounted Device
VSWR	Voltage Standing-Wave Ratio
WCS	Wireless Communications Service
WiMAX	Worldwide Interoperability for Microwave Access

## 11. Revision history

**Table 12. Revision history**

Document ID	Release date	Data sheet status	Change notice	Supersedes
BLF6G38-25_BLF6G38S-25_2	20081223	Product data sheet	-	BLF6G38-25_BLF6G38S-25_1
Modifications:				
			<ul style="list-style-type: none"> <li>Changed the maximum drain current and the maximum junction temperature in <a href="#">Table 4 on page 2</a></li> <li>Moved impedance information to <a href="#">Section 8</a></li> </ul>	
BLF6G38-25_BLF6G38S-25_1	20080218	Preliminary data sheet	-	-

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### 12.1 Data sheet status

Document status <sup>[1][2]</sup>	Product status <sup>[3]</sup>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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